

2SB1470

Silicon PNP triple diffusion planar type darlington

For power amplification

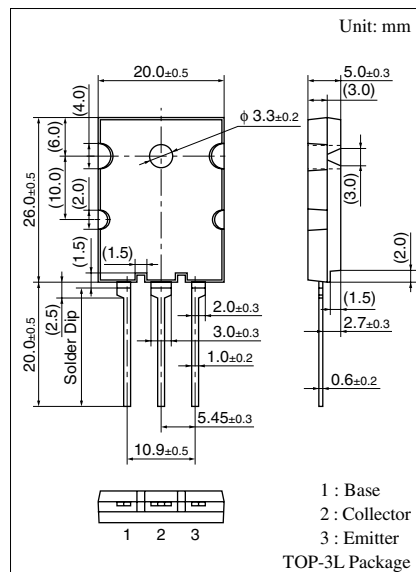
Complementary to 2SD2222

■ Features

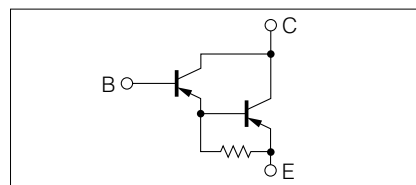
- Optimum for 120 W Hi-Fi output
- High forward current transfer ratio h_{FE}
- Low collector to emitter saturation voltage $V_{CE(sat)}$

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Collector to base voltage	V_{CBO}	-160	V	
Collector to emitter voltage	V_{CEO}	-160	V	
Emitter to base voltage	V_{EBO}	-5	V	
Peak collector current	I_{CP}	-15	A	
Collector current	I_C	-8	A	
Collector power dissipation	$T_C = 25^\circ\text{C}$	P_C	150	W
		$T_a = 25^\circ\text{C}$	3.5	
Junction temperature	T_j	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	



Internal Connection



■ Electrical Characteristics $T_C = 25^\circ\text{C}$

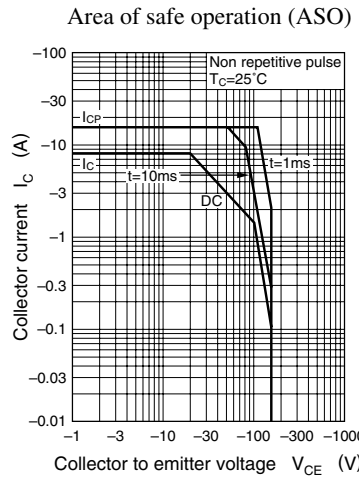
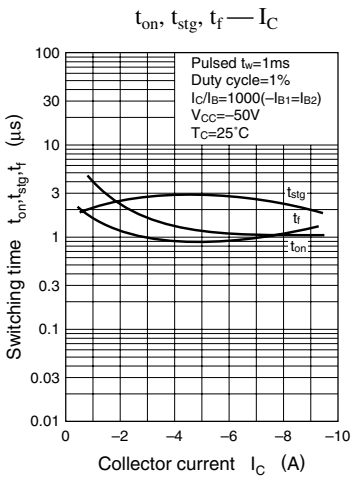
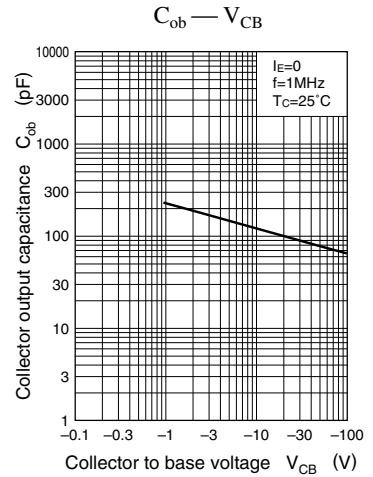
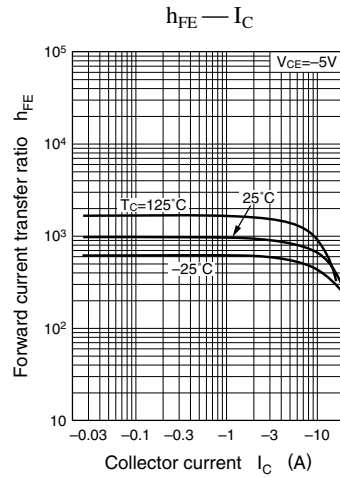
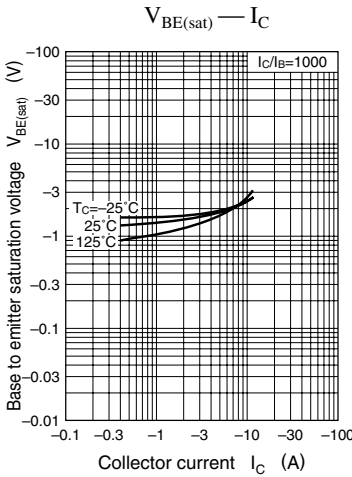
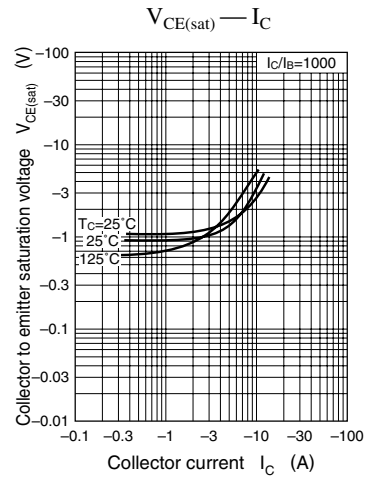
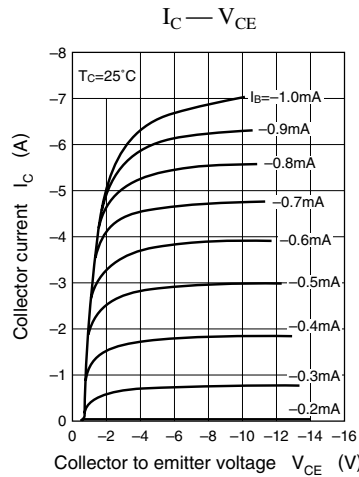
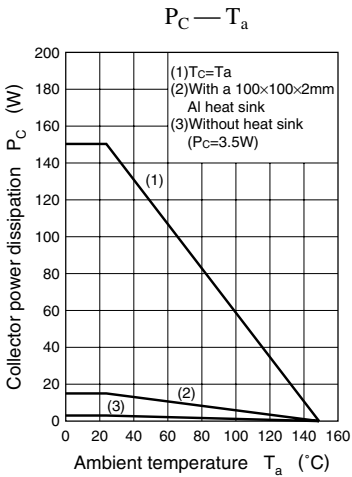
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -160\text{ V}, I_E = 0$			-100	μA
	I_{CEO}	$V_{CE} = -160\text{ V}, I_B = 0$			-100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$			-100	μA
Collector to emitter voltage	V_{CEO}	$I_C = -30\text{ mA}, I_B = 0$	-160			V
Forward current transfer ratio	h_{FE1}	$V_{CE} = -5\text{ V}, I_C = -1\text{ A}$	1 000			
	h_{FE2}^*	$V_{CE} = -5\text{ V}, I_C = -7\text{ A}$	3 500		20 000	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -7\text{ A}, I_B = -7\text{ mA}$			-3	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -7\text{ A}, I_B = -7\text{ mA}$			-3	V
Transition frequency	f_T	$V_{CE} = -10\text{ V}, I_C = -0.5\text{ A}, f = 1\text{ MHz}$		20		MHz
Turn-on time	t_{on}	$I_C = -7\text{ A}, I_{B1} = -7\text{ mA}, I_{B2} = 7\text{ mA}, V_{CC} = -50\text{ V}$		1		μs
Storage time	t_{stg}			1.5		μs
Fall time	t_f			1.2		μs

Note) *: Rank classification

Rank	Q	S
h_{FE2}	3 500 to 10 000	7 000 to 20 000

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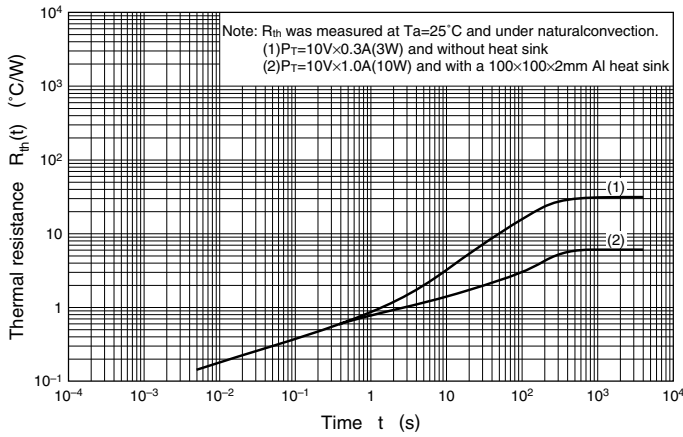
Power Transistors



Power Transistors

2SB1470

$$R_{th(t)} - t$$



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